

SGGS182M

MONO-Crystalline



Technical Data and Design

Dimension 182mm?182mm±0.5 247mm

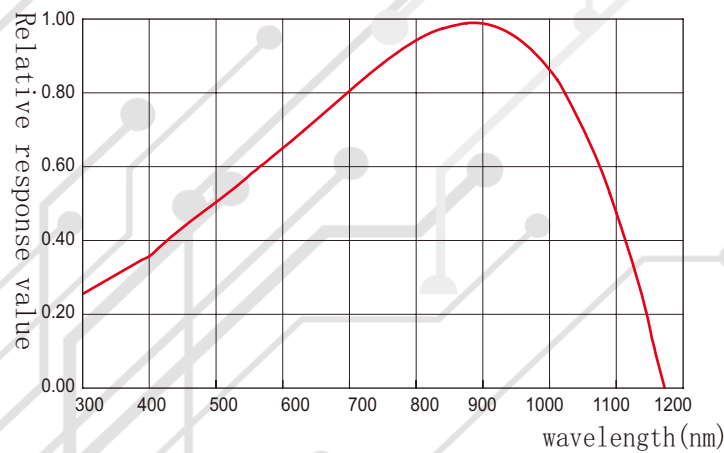
Diameter 247mm±0.25mm

Thickness 190µm±30µm (Excluding positive silver thickness)

Front(-) 0.06mm wide main gate, 132 auxiliary gates,
blue silicon nitride antireflection film

Back(+) 6 sections of 1.8mm silver pads are embedded in 1.4mm
aluminum main grid and 162 aluminum auxiliary grids

Spectral response characteristics



Thermal Characteristics

PARAMETERS	UNIT	MEASUREMENT
α_{Isc}	[%/°C]	0.060
β_{Voc}	[%/°C]	-0.300
γ_{Pmax}	[%/°C]	-0.390

The above data are compiled based on the existing Gstar plant process and equipment conditions, and Gstar energy reserves the right of final interpretation.

Electrical Performance Parameters

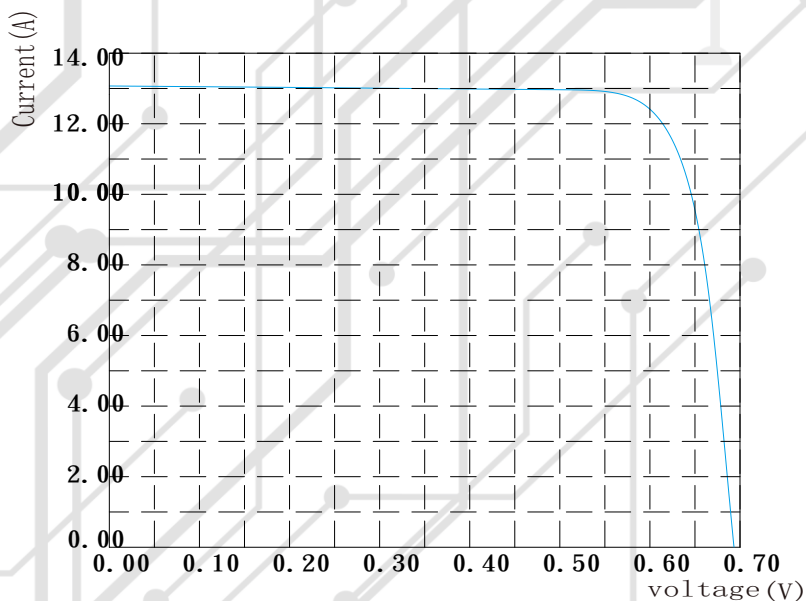
NCell (%)	Pmpp (W)	Vmp (V)	Imp (A)	Voc (V)	Isc (A)
?23.0	7.59	0.5907	12.854	0.6904	13.521
22.90-23.0	7.56	0.5889	12.839	0.6884	13.505
22.80-22.90	7.53	0.5870	12.824	0.6864	13.489
22.70-22.80	7.49	0.5852	12.807	0.6854	13.472
22.60-22.70	7.46	0.5834	12.790	0.6836	13.454
22.50-22.60	7.43	0.5815	12.774	0.6827	13.437
22.40-22.50	7.40	0.5798	12.756	0.6818	13.418
22.30-22.40	7.36	0.5779	12.740	0.6801	13.401
22.20-22.30	7.33	0.5757	12.732	0.6783	13.393
22.10-22.20	7.30	0.5740	12.711	0.6782	13.371
22.00-22.10	7.26	0.5721	12.696	0.6772	13.355
21.90-22.00	7.23	0.5703	12.677	0.6763	13.335

Note: double sided rate(Back Pmpp/Front Pmpp,Back Isc/Front Isc)_{min}≥70%

I-V characteristics under low illumination

Intensity [W/m ²]	Voc [%]	Isc [%]	Pmpo [%]
1000	100.00	100.00	100.00
800	99.10	80.08	80.24
600	97.84	60.00	59.99
400	96.22	40.00	39.68
200	93.32	19.98	19.30

IV Curve



Gstar

COMPANY NAME: G-STAR PTE. LTD.
 FACTORY ADD: 6 RAFFLES QUAY #14-06
 SINGAPORE 048580
 E-MAIL:lyntonlin@gstar-solar.com
 WEBSITE: www.gstar.sg